

STARPOWER

SEMICONDUCTOR

IGBT

GD150HFU120C6S

1200V/150A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

Features

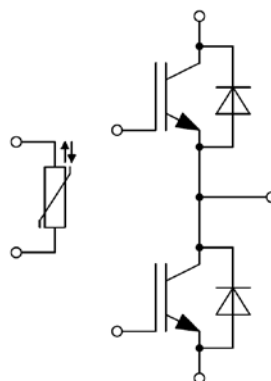
- NPT IGBT technology
- 10 μ s short circuit capability
- Low switching losses
- Rugged with ultrafast performance
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	230	A
	@ $T_C=80^{\circ}\text{C}$	150	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	300	A
P_D	Maximum Power Dissipation @ $T_j=150^{\circ}\text{C}$	1179	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	150	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	300	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	150	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +125	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=150\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		2.90	3.35	V	
		$I_C=150\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		3.60			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=3.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.0	6.1	7.0	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			5.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			0.8		Ω	
C_{ies}	Input Capacitance			19.2		nF	
C_{res}	Reverse Transfer Capacitance	$V_{CE}=30\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		0.60		nF	
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		1.83		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=150\text{A}, R_G=4.3\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		203		ns	
t_r	Rise Time			49		ns	
$t_{d(off)}$	Turn-Off Delay Time			261		ns	
t_f	Fall Time			136		ns	
E_{on}	Turn-On Switching Loss				12.6		mJ
E_{off}	Turn-Off Switching Loss				4.92		mJ
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=600\text{V}, I_C=150\text{A}, R_G=4.3\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		203		ns
t_r	Rise Time				50		ns
$t_{d(off)}$	Turn-Off Delay Time			271		ns	
t_f	Fall Time			172		ns	
E_{on}	Turn-On Switching Loss				16.5		mJ
E_{off}	Turn-Off Switching Loss				7.23		mJ
I_{SC}	SC Data	$t_P \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$			975		A

Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=150\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		2.25	2.70	V
		$I_F=150\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		2.35		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=150\text{A},$ $-di/dt=3000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		10.5		μC
I_{RM}	Peak Reverse Recovery Current			123		A
E_{rec}	Reverse Recovery Energy			4.14		mJ
Q_r	Recovered Charge			20.1		μC
I_{RM}	Peak Reverse Recovery Current		$V_R=600\text{V}, I_F=150\text{A},$ $-di/dt=3000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		168	
E_{rec}	Reverse Recovery Energy			9.48		mJ

NTC Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		k Ω
$\Delta R/R$	Deviation of R_{100}	$T_C=100^\circ\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K
$B_{25/80}$	B-value	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15\text{K}))]$		3411		K
$B_{25/100}$	B-value	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15\text{K}))]$		3433		K

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		20		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		1.10		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.106	K/W
	Junction-to-Case (per Diode)			0.260	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.025		K/W
	Case-to-Heatsink (per Diode)		0.062		
	Case-to-Heatsink (per Module)		0.009		
M	Terminal Connection Torque, Screw M6	3.0		6.0	N.m
	Mounting Torque, Screw M5	3.0		6.0	
G	Weight of Module		350		g

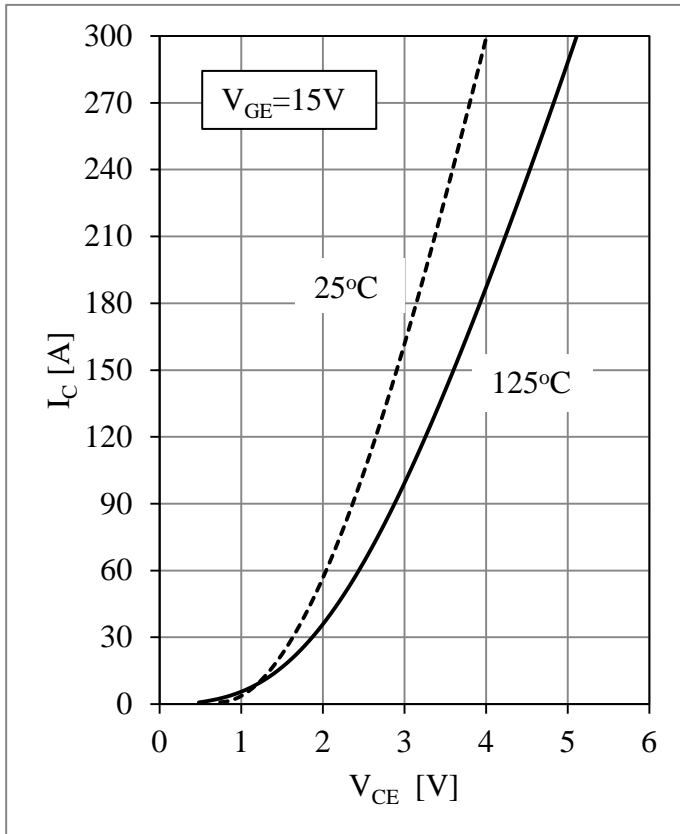


Fig 1. IGBT Output Characteristics

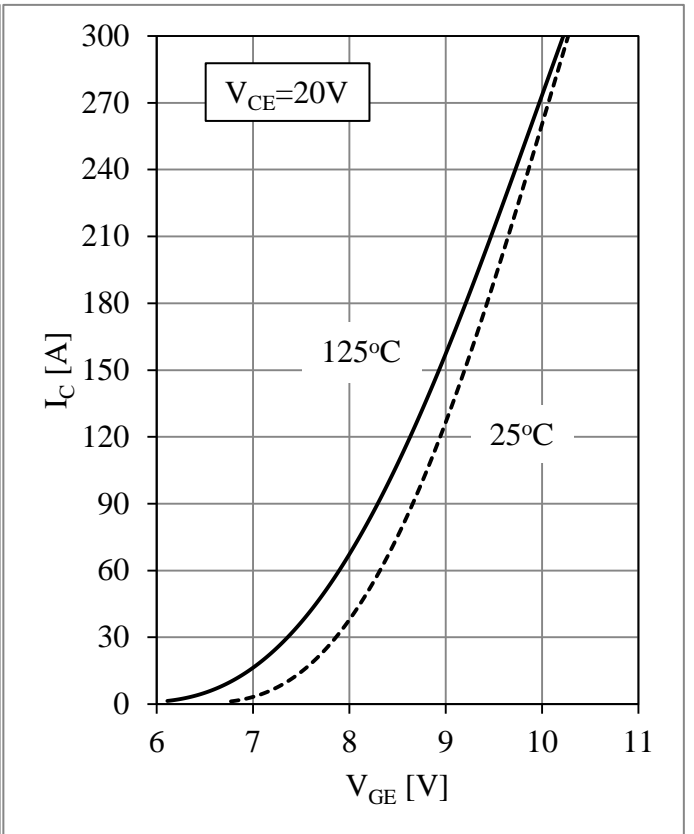


Fig 2. IGBT Transfer Characteristics

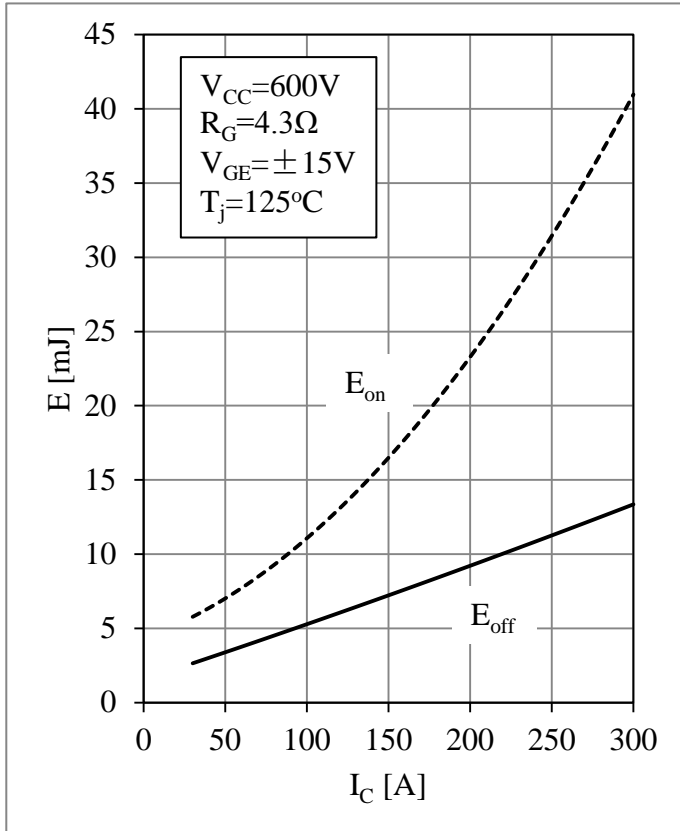


Fig 3. IGBT Switching Loss vs. I_C

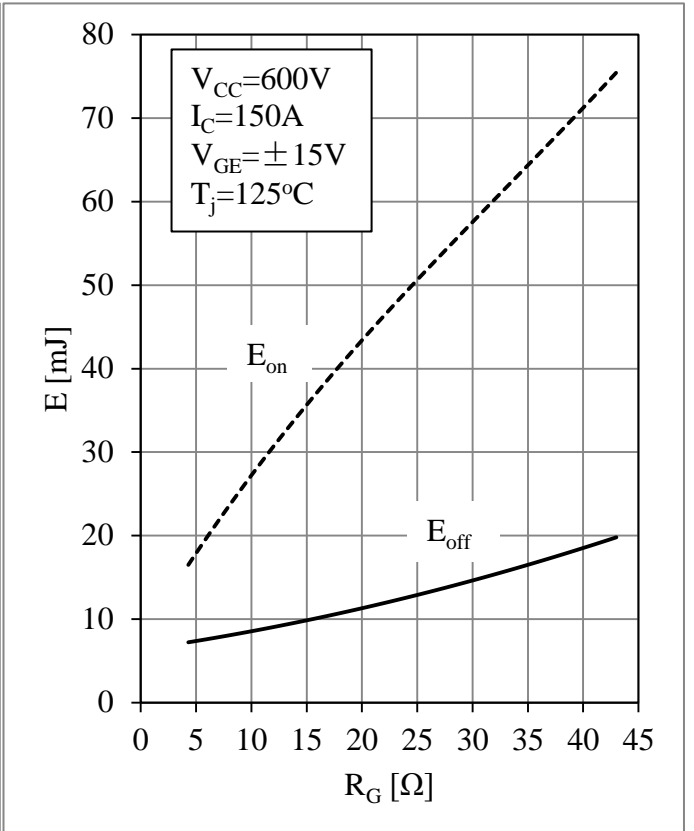


Fig 4. IGBT Switching Loss vs. R_G

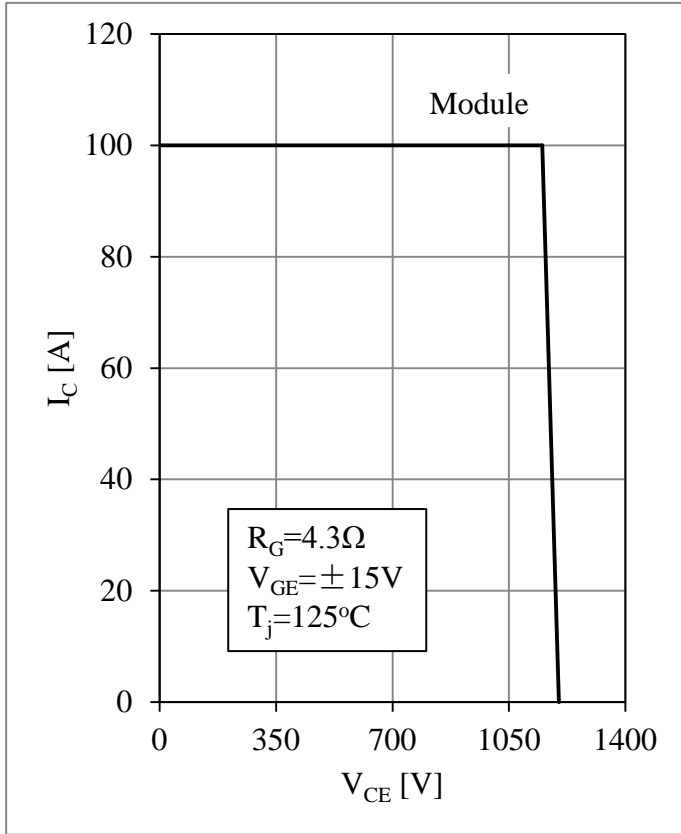


Fig 5. RBSOA

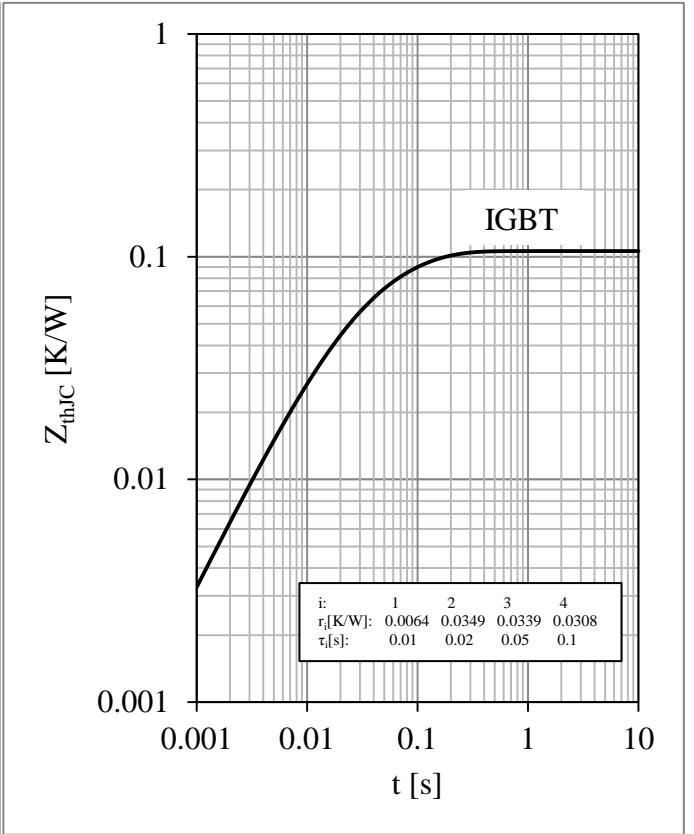


Fig 6. IGBT Transient Thermal Impedance

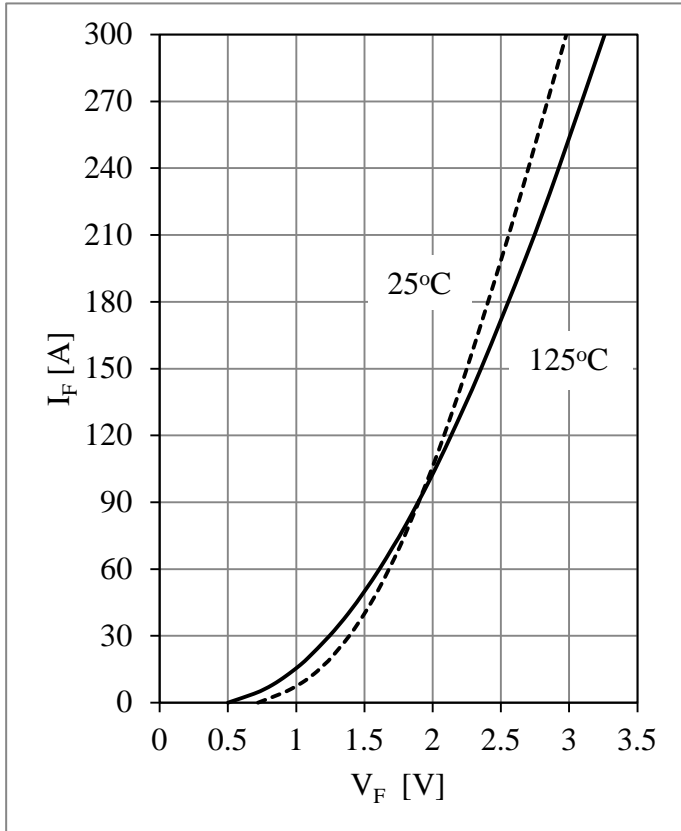


Fig 7. Diode Forward Characteristics

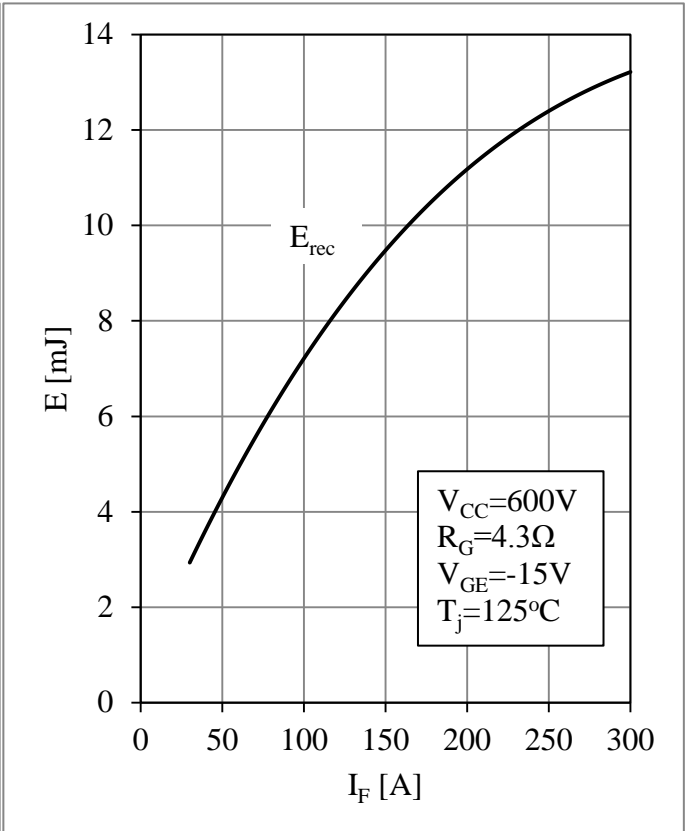


Fig 8. Diode Switching Loss vs. I_F

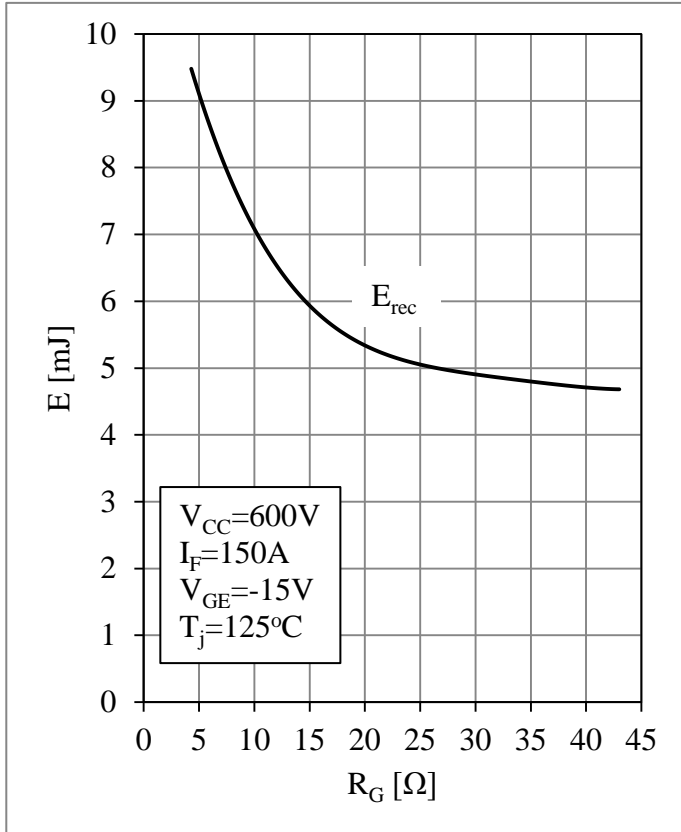


Fig 9. Diode Switching Loss vs. R_G

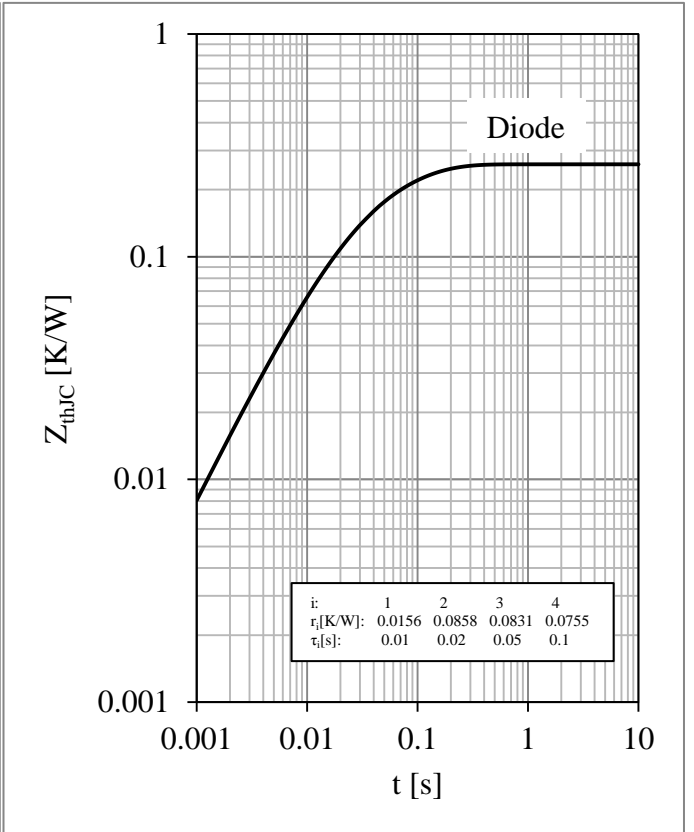


Fig 10. Diode Transient Thermal Impedance

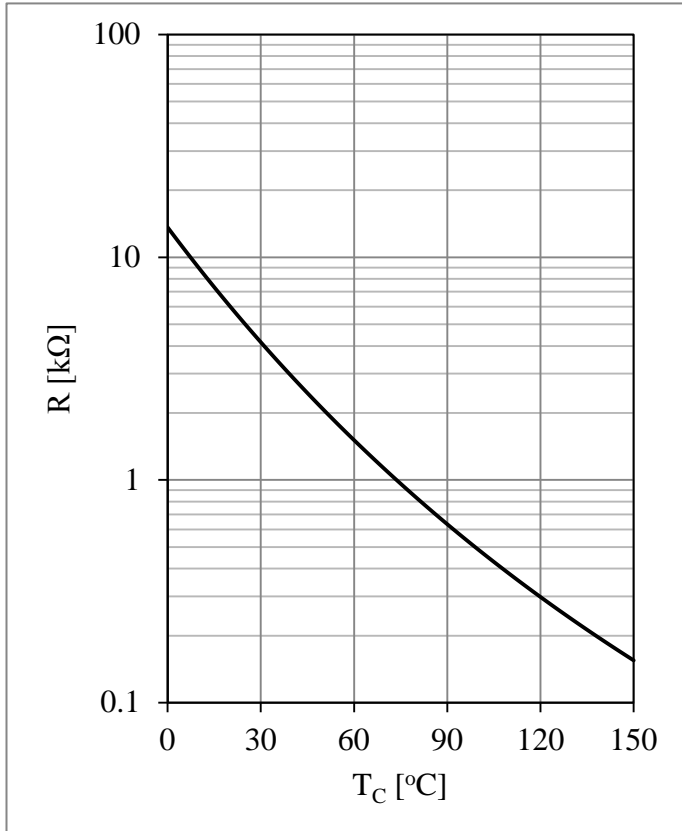
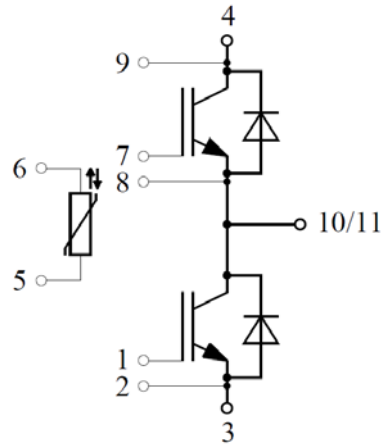


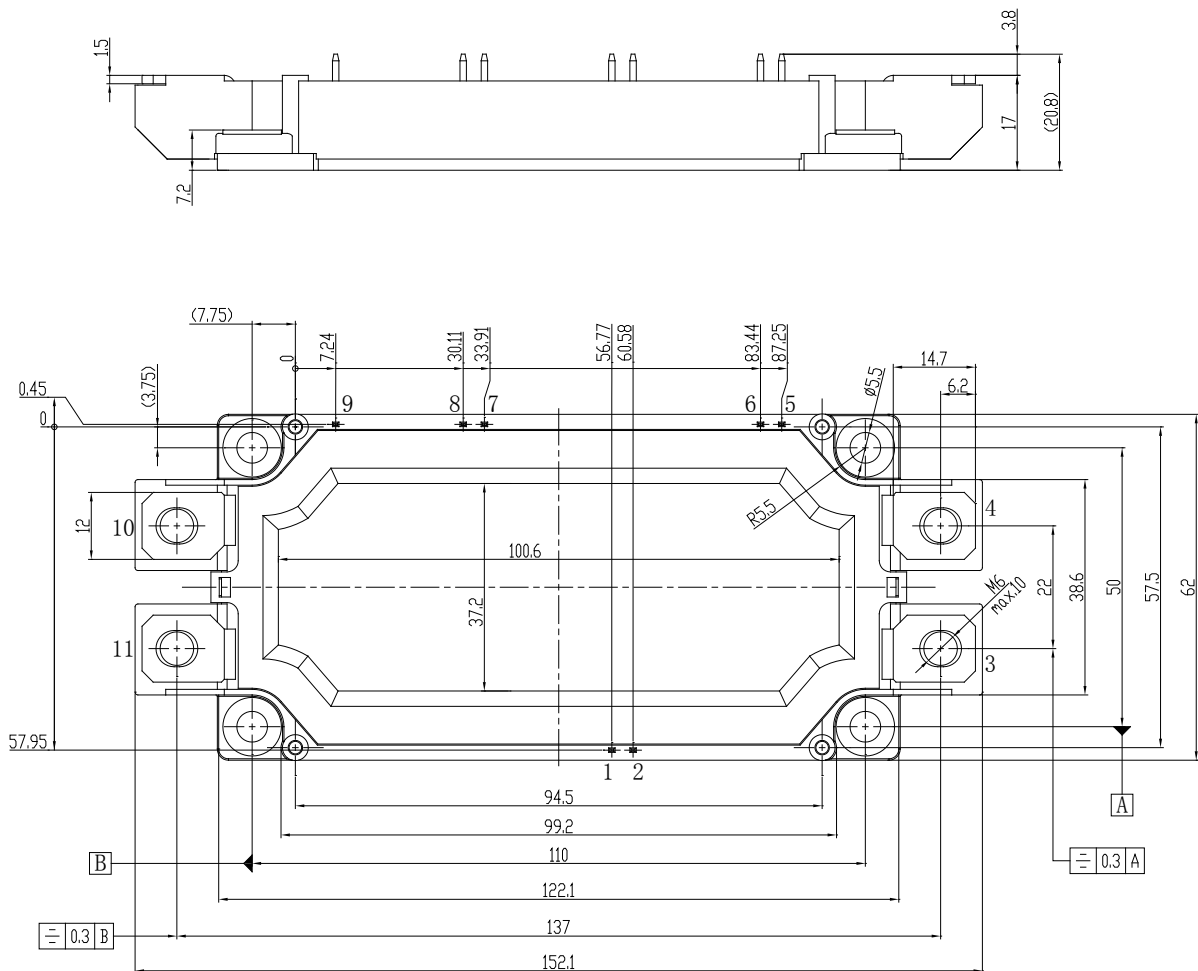
Fig 11. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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